

NPN EPITAXIAL SILICON TRANSISTOR

GENERAL PURPOSE TRANSISTOR

* Feature:

(1) Low Cob.

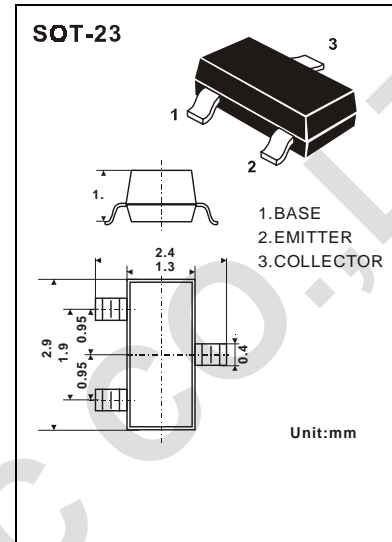
Cob=2.0pF

(2) Complements the 2SA1037AK/2SA1576/

2SA1774/2SA1774H/2SA2029/2SA933AS.

ABSOLUTE MAXIMUM RATINGS at Ta=25°C

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	Vceo	50	V
Collector-Base Voltage	Vcbo	60	V
Collector Current	Ic	0.15	A
Collector Dissipation Ta=25°C*	P _D	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-150	°C



ELECTRICAL CHARACTERISTICS at Ta=25°C

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	60			V	Ic= 50uA
Collector-Emitter Breakdown Voltage#	BVceo	50			V	Ic= 1mA
Emitter-Base Breakdown Voltage	BVebo	7			V	Ie= 50uA
Collector-Base Cutoff Current	Icbo			0.1	uA	Vcb= 60V
Emitter-Base Cutoff Current	Iebo			0.1	uA	Veb=7V
DC Current Gain	Hfe	120		560		Vce= 6V Ic= 1mA
Collector-Emitter Saturation Voltage	Vce(sat)			0.4	V	Ic= 50mA Ib= 5mA
Output Capacitance	Cob		2	3.5	PF	Vcb= 12V Ie=0 f=1MHz
Current Gain-Bandwidth Product	f _T		180		MHz	Vce= 12V Ie= -2mA f=100MHZ

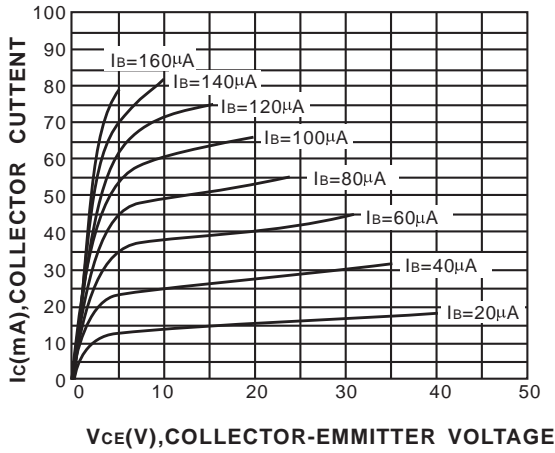
* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25°C.

Pulse Test: Pulse Width ≤300uS,Duty cycle ≤2%

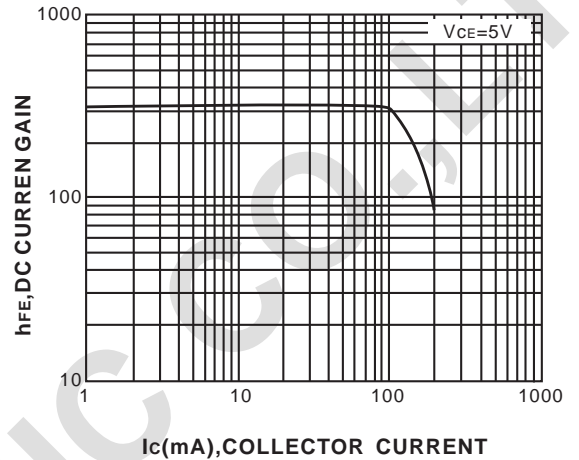
DEVICE MARKING:

2SC2412K=HF

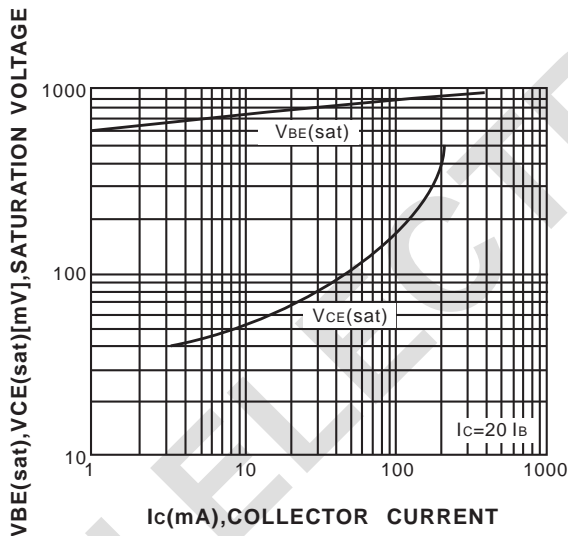
Typical Characteristics



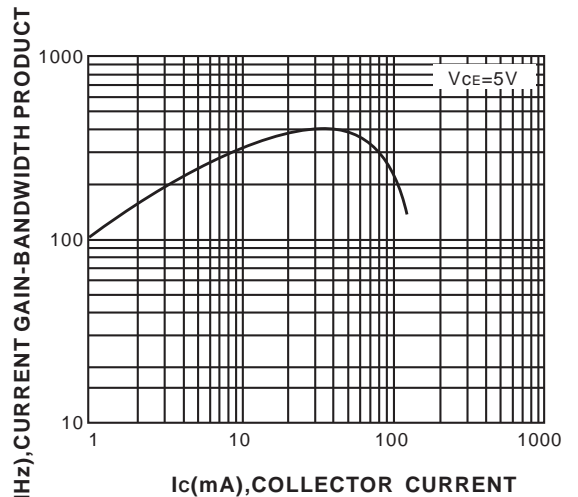
Static Characteristic



DC Current Gain



**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Current Gain Bandwidth Product